### 5. Thermal Characteristics

| Characteristics                       | Symbol                | Max  | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 1.72 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 83.3 |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted with heatsink so that  $R_{th(ch-a)}$  becomes 4.16°C/W.

Note 3: V\_DD = 80 V, T\_ch = 25°C (initial), L = 77.6  $\mu$ H, I<sub>AR</sub> = 22 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

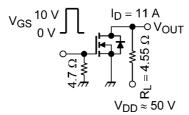
## 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics                         | Symbol               | Test Condition                                  | Min | Тур. | Max  | Unit |
|---|----------------------|---|-----|------|------|------|
| Gate leakage current                    | I <sub>GSS</sub>     | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V                | _   | —    | ±0.1 | μA   |
| Drain cut-off current                   | I <sub>DSS</sub>     | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V  | _   | —    | 10   |      |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 100 | _    | _    | V    |
| Drain-source breakdown voltage (Note 4) | V <sub>(BR)DSX</sub> | $I_{D}$ = 10 mA, $V_{GS}$ = -20 V               | 65  | —    | —    |      |
| Gate threshold voltage                  | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.3 mA | 2.0 | —    | 4.0  |      |
| Drain-source on-resistance              | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11 A   | _   | 11.5 | 13.8 | mΩ   |

Note 4: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

## 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 1800 | —   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _   | 18   | _   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 310  | —   |      |
| Gate resistance                | r <sub>g</sub>   | _  | _   | 2.0  | —   | Ω    |
| Switching time (rise time)     | tr               | See Figure 6.2.1   | _   | 11   | —   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | _   | 27   | —   |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | _   | 11   | —   |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | _   | 38   | _   |      |



 $Duty \le 1\%, \ t_w = 10 \ \mu s$  Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 80 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 22 \text{ A}$ | —   | 28   | —   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | —   | 8.7  | —   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  | 1  | _   | 8.1  | _   |      |
| Gate switch charge                              | Q <sub>SW</sub>  | ]  |     | 12   |     |      |

## 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                |          | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|--------------------------------|----------|------------------|---|-----|------|------|------|
| Reverse drain current (DC)     | (Note 5) | I <sub>DR</sub>  | —   | _   | _    | 22   | А    |
| Reverse drain current (pulsed) | (Note 5) | I <sub>DRP</sub> | _   |     |      | 102  |      |
| Diode forward voltage          |          | V <sub>DSF</sub> | I <sub>DR</sub> = 22 A, V <sub>GS</sub> = 0 V | _   | —    | -1.2 | V    |
| Reverse recovery time          | (Note 6) | t <sub>rr</sub>  | I <sub>DR</sub> = 22 A, V <sub>GS</sub> = 0 V |     | 54   |      | ns   |
| Reverse recovery charge        | (Note 6) | Q <sub>rr</sub>  | -dl <sub>DR</sub> /dt = 100 A/μs              |     | 94   |      | nC   |

Note 5: Ensure that the channel temperature does not exceed 150°C. Note 6: Ensure that  $V_{DS}$  peak does not exceed  $V_{DSS}$ .

## 7. Marking

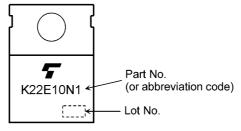
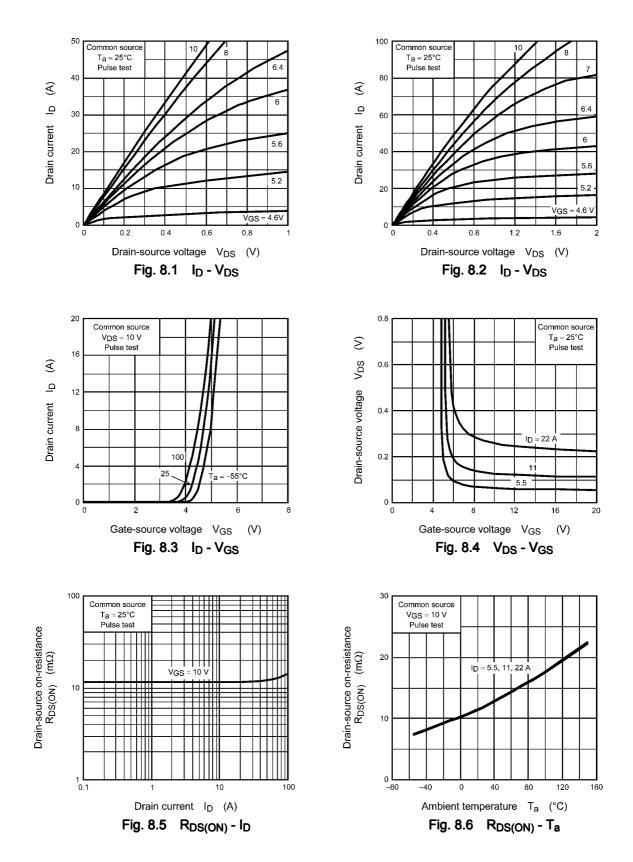


Fig. 7.1 Marking

## 8. Characteristics Curves (Note)



100

20

16

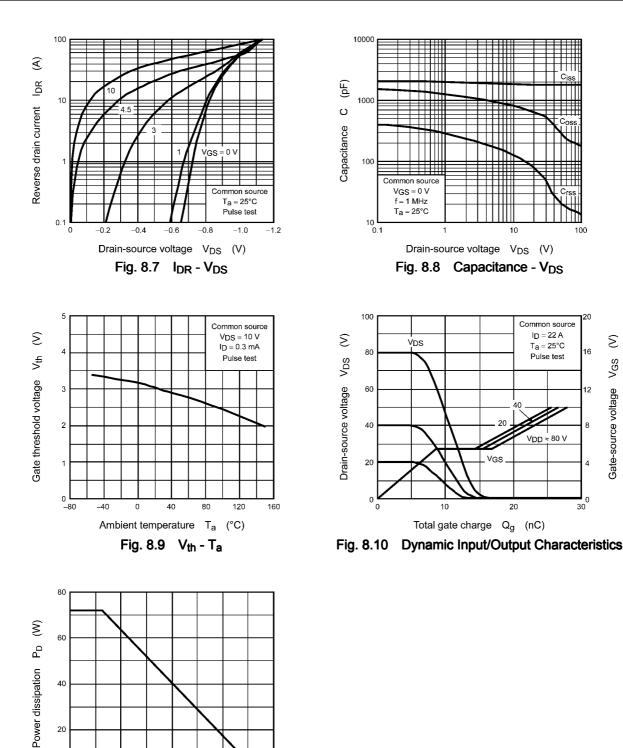
12

8

30 30

S

Gate-source voltage V<sub>GS</sub>



0 L

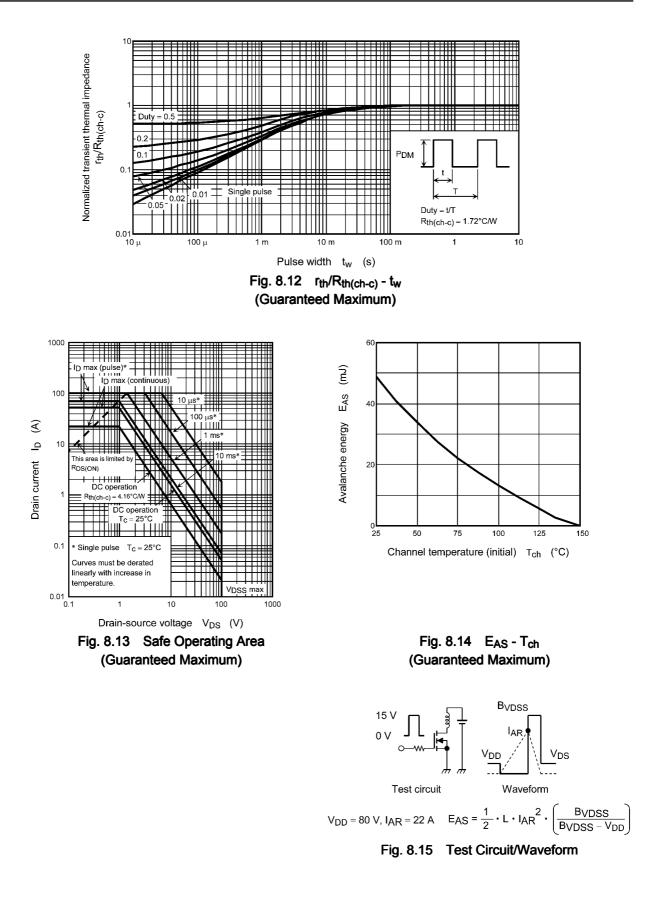
80

Case temperature  $T_c$  (°C) Fig. 8.11 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

40

120

160



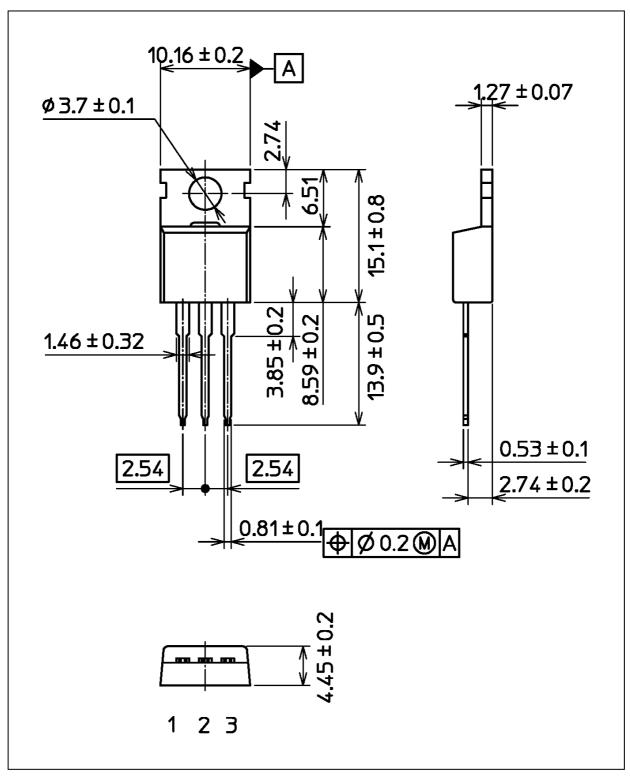
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

TK22E10N1





Weight: 1.93 g (typ.)

|                  | Package Name(s) |  |
|------------------|-----------------|--|
| TOSHIBA: 2-10X1A |                 |  |
| Nickname: TO-220 |                 |  |

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